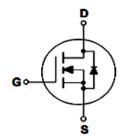




# N-Channel Plastic-Encapsulate MOSFET

60V , 500mA



BS170

TO-92 Plastic Package RoHS compliant

## FEATURES:

- 1. High Density Cell Design for Low  $R_{\text{DS}(\text{ON})}$
- 2. Voltage Controlled Small Signal Switch
- 3. Rugged and reliable

TO-92

4. High saturation current capability

## **ABSOLUTE MAXIMUM RATINGS** (Ta = 25 °C Unless otherwise specified)

PARAMETER		SYMBOL	VALUE	UNIT
Drain-Source voltage		V <sub>DSS</sub>	60	V
Drain-Gate Voltage (R <sub>GS</sub> ≤1MΩ)		V <sub>DGR</sub>	60	V
Gate-Source voltage		V <sub>GSS</sub>	±20	V
Drain Current	Continuous		500	mA
	Pulsed	' I <sub>D</sub>	1200	— mA
Maximum Power Dissipation		P <sub>D</sub>	830	mW
Derate Above 25°C			6.6	mW/°C
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C
Maximum Lead Temperature for Soldering Purposes, 1/16" from Case for 10 Seconds		Τ <sub>L</sub>	300	°C

## THERMAL RESISTANCE

Thermal Resistance, Junction-to-Ambient	$R_{ extsf{ heta}JA}$	150	°C/W

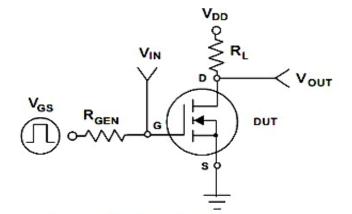




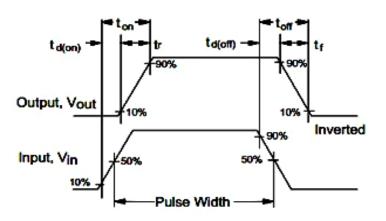
## ELECTRICAL CHARACTERISTICS at (Ta = 25 °C Unless otherwise specified)

PARAMETER SYMBOL TEST CONDIT		TEST CONDITION	VALUE		UNIT	
PARAMETER	STIVIDUL	TEST CONDITION	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage	B <sub>VDSS</sub>	$V_{GS} = 0V, I_{D} = 100\mu A$	60			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 25V, V_{GS} = 0V$			0.5	μA
Gate-body Leakage	$I_{GSF}$	V <sub>GS</sub> = 15V, V <sub>DS</sub> = 0V,			10	nA
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 1mA$	0.8	2.1	3	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> = 200mA		1.2	5	Ω
Forward Trans conductance	g <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =200mA		320		mS
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V		24	40	
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 10V		17	30	pF
Reverse Transfer Capacitance	C <sub>rss</sub>	f = 1.0MHz		7	10	
Turn-On Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 25V, I <sub>D</sub> = 200mA,			10	20
Turn-Off Time	$t_{d(off)}$	V <sub>GS</sub> = 10V, R <sub>GEN</sub> = 25W			10	ns

### **TEST CIRCUIT AND DIAGRAMS**



Switching Test Circuit



Switching Waveforms

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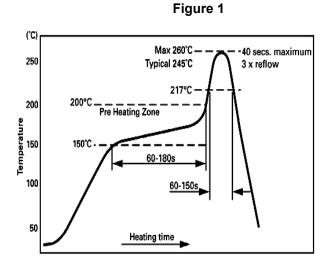


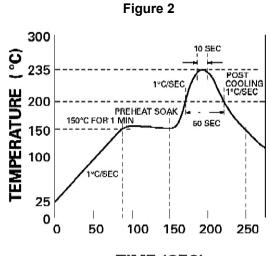
#### **Recommended Reflow Solder Profiles**

The recommended reflow solder profiles for Pb and Pb-free devices are shown below.

Figure 1 shows the recommended solder profile for devices that have Pb-free terminal plating, and where a Pb-free solder is used.

Figure 2 shows the recommended solder profile for devices with Pb-free terminal plating used with leaded solder, or for devices with leaded terminal plating used with a leaded solder.





TIME (SEC)

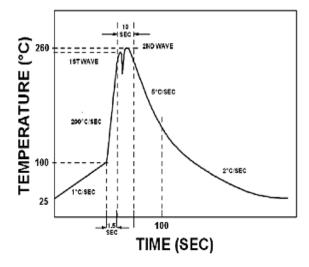
Reflow profiles in tabular form				
Profile Feature	Sn-Pb System	Pb-Free System		
Average Ramp-Up Rate	~3°C/second	~3°C/second		
Preheat				
– Temperature Range	150-170°C	150-200°C		
– Time	60-180 seconds	60-180 seconds		
Time maintained above:				
– Temperature	200°C	217°C		
– Time	30-50 seconds	60-150 seconds		
Peak Temperature	235°C	260°C max.		
Time within +0 -5°C of actual Peak	10 seconds	40 seconds		
Ramp-Down Rate	3°C/second max.	6°C/second max.		

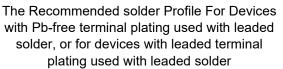


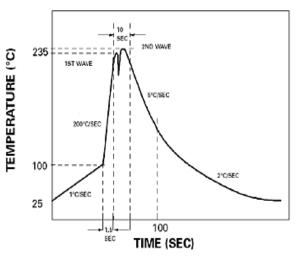


### **Recommended Wave Solder Profiles**

The Recommended solder Profile For Devices with Pb-free terminal plating where a Pb-free solder is used







Wave Profiles in Tabular Form				
Profile Feature	Sn-Pb System	Pb-Free System		
Average Ramp-Up Rate	~200°C/second	~200°C/second		
Heating rate during preheat	Typical 1-2, Max 4°C/sec	Typical 1-2, Max 4°C/Sec		
Final preheat Temperature	Within 125°C of Solder Temp	Within 125°C of Solder Temp		
Peak Temperature	235°C	260°C max.		
Time within +0 -5°C of actual Peak	10 seconds	10 seconds		
Ramp-Down Rate	5°C/second max.	5°C/second max		





## **TYPICAL CHARACTERISTICS CURVES**

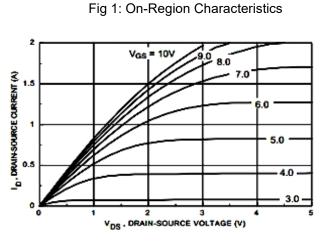
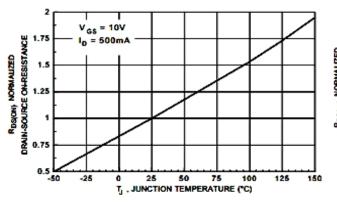
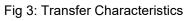


Fig 2: On-Resistance Variation with Temperature





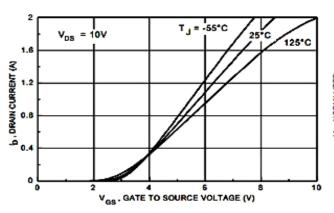


Fig 4: On-Resistance Variation with Gate Voltage and Drain Current

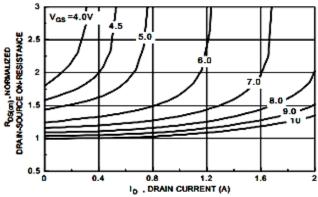


Fig 5: On-Resistance Variation with Drain Current and Temperature

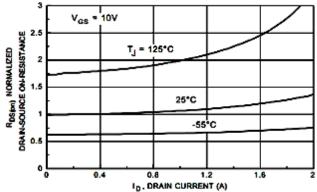
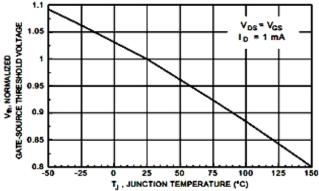


Fig 6: Gate Threshold Variation with Temperature



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Fig 7: Breakdown Voltage Variation



## **TYPICAL CHARACTERISTICS CURVES**

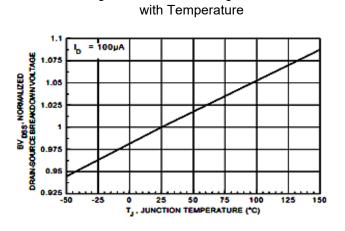


Fig 8: Capacitance Characteristics

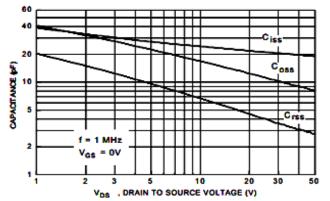


Fig 9: BS170 Maximum Safe Operating Area

Fig 10: Body Diode Forward Voltage Variation with Current and Temperature

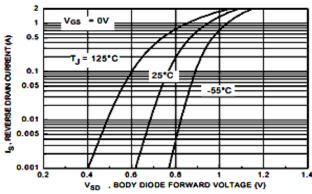


Fig 11: Gate Charge Characteristics

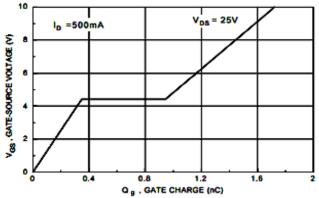
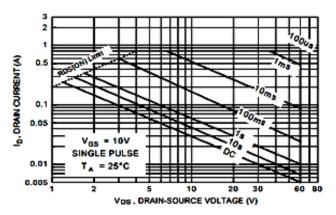


Fig 12: MMBF 170 Maximum Safe Operating Area



ID. DRAN CURRENT (A) 0.5 0.1 0 0.05 Vas = 10V SINGLE PULSE Т Т. = 25°C 0.01 0.005 10 20 30 60 80 Vps. DRAIN-SOURCE VOLTAGE (V)

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# **TYPICAL CHARACTERISTICS CURVES**

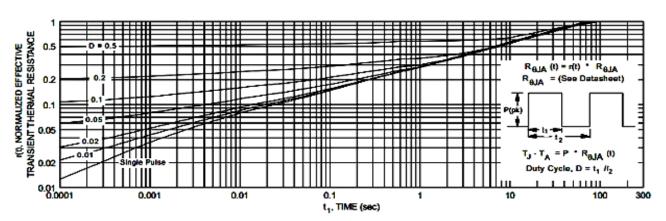
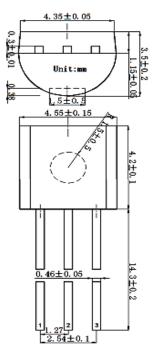


Fig 13: TO-92, BS170 Transient Thermal Response Curve





# PACKAGE DETAILS

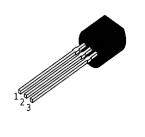


TO-92 Plastic Package

All dimensions are in mm

## **Pin Configuration**

- 1. Drain
- 2. Gate
- 3. Source







## Recommended Product Storage Environment for Discrete Semiconductor Devices

This storage environment assumes that the Diodes and transistors are packed properly inside the original packing supplied by CDIL.

- · Temperature 5 °C to 30 °C
- · Humidity between 40 to 70 %RH
- · Air should be clean.
- · Avoid harmful gas or dust.
- · Avoid outdoor exposure or storage in areas subject to rain or water spraying .
- Avoid storage in areas subject to corrosive gas or dust. Product shall not be stored in areas exposed to direct sunlight.
- · Avoid rapid change of temperature.
- · Avoid condensation.
- · Mechanical stress such as vibration and impact shall be avoided.
- · The product shall not be placed directly on the floor.
- The product shall be stored on a plane area. They should not be turned upside down. They should not be placed against the wall.

#### Shelf Life of CDIL Products

The shelf life of products is the period from product manufacture to shipment to customers. The product can be unconditionally shipped within this period. The period is defined as 2 years.

If products are stored longer than the shelf life of 2 years the products shall be subjected to quality check as per CDIL quality procedure.

The products are further warranted for another one year after the date of shipment subject to the above conditions in CDIL original packing.

#### Floor Life of CDIL Products and MSL Level

When the products are opened from the original packing, the floor life will start. For this, the following JEDEC table may be referred:

JEDEC MSL Level				
Level	Time	Condition		
1	Unlimited	≤30 °C / 85% RH		
2	1 Year	≤30 °C / 60% RH		
2a	4 Weeks	≤30 °C / 60% RH		
3	168 Hours	≤30 °C / 60% RH		
4	72 Hours	≤30 °C / 60% RH		
5	48 Hours	≤30 °C / 60% RH		
5a	24 Hours	≤30 °C / 60% RH		
6	Time on Label(TOL)	≤30 °C / 60% RH		





## **Customer Notes**

### **Component Disposal Instructions**

- 1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
- 2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

### Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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